



SANYO Semiconductors

DATA SHEET

2SB892 / 2SD1207

— ~~PNP~~ NPN Epitaxial Planar Silicon Transistors

Large-Current Switching Applications

Applications

- Power supplies, relay drivers, lamp drivers, and automotive wiring.

Features

- FBET and MBIT processed (Original process of SANYO).
- Low saturation voltage.
- Large current capacity and wide ASO.

Specifications (—) : 2SB892

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(—)60	V
Collector-to-Emitter Voltage	VCEO		(—)50	V
Emitter-to-Base Voltage	VEBO		(—)6	V
Collector Current	IC		(—)2	A
Collector Current (Pulse)	ICP		(—)4	A
Collector Dissipation	PC		1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	VCB=(—)50V, IE=0A			(—)0.1	μA
Emitter Cutoff Current	IEBO	VEB=(—)4V, IC=0A			(—)0.1	μA

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SANYO Semiconductor Co., Ltd.

www.semiconductor-sanyo.com/network

2SB892 / 2SD1207

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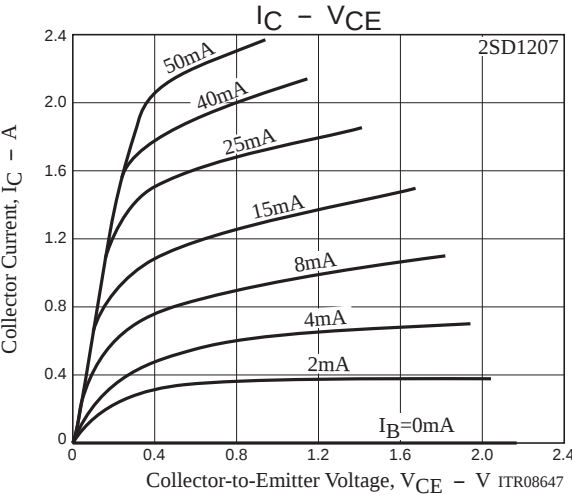
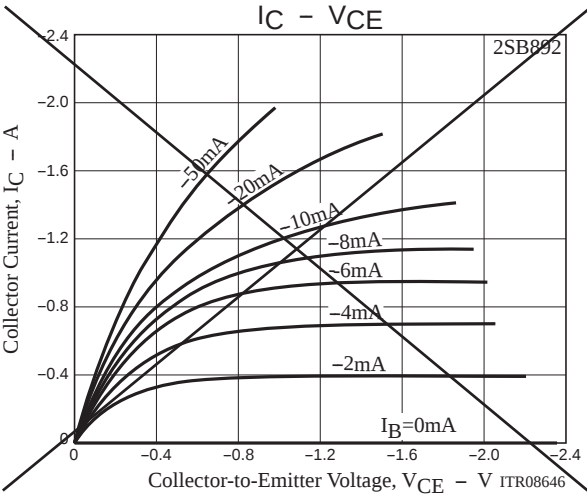
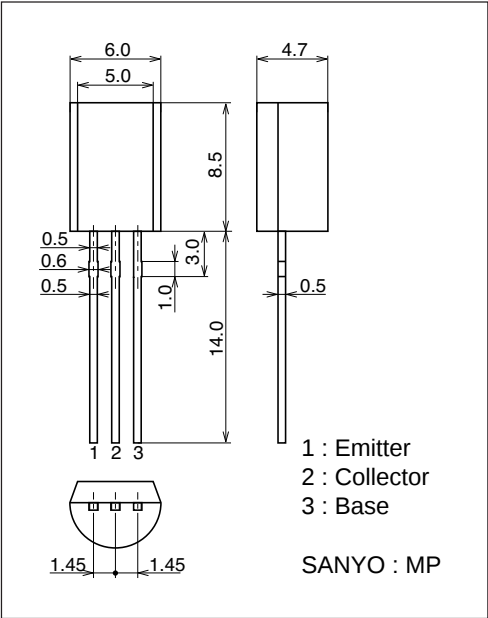
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
DC Current Gain	h_{FE1}^*	$V_{CE} = (\pm)2V, I_C = (\pm)100mA$	100		560	
	h_{FE2}	$V_{CE} = (\pm)2V, I_C = (\pm)1.5A$	40			
Gain-Bandwidth Product	f_T	$V_{CE} = (\pm)10V, I_C = (\pm)50mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB} = (\pm)10V, f = 1MHz$		(22)12		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (\pm)1A, I_B = (\pm)50mA$		(=0.3)0.15	(=0.7)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = (\pm)1A, I_B = (\pm)50mA$		(=)0.9	(=)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (\pm)10\mu A, I_E = 0A$	(=)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (\pm)1mA, R_{BE} = \infty$	(=)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (\pm)10\mu A, I_C = 0A$	(=)6			V

* : The 2SB892 / 2SD1207 are graded as follows by h_{FE} at 100mA :

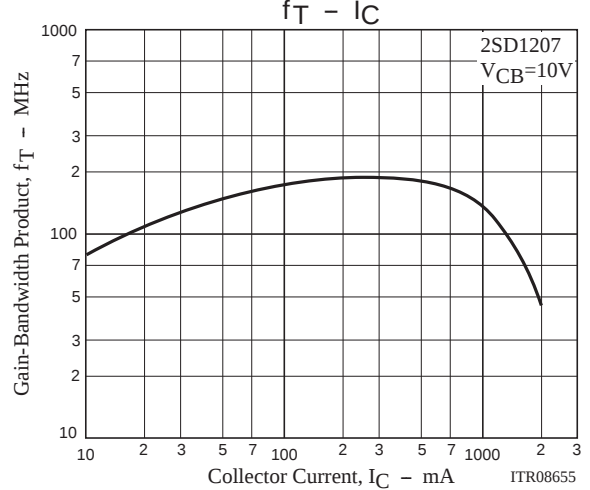
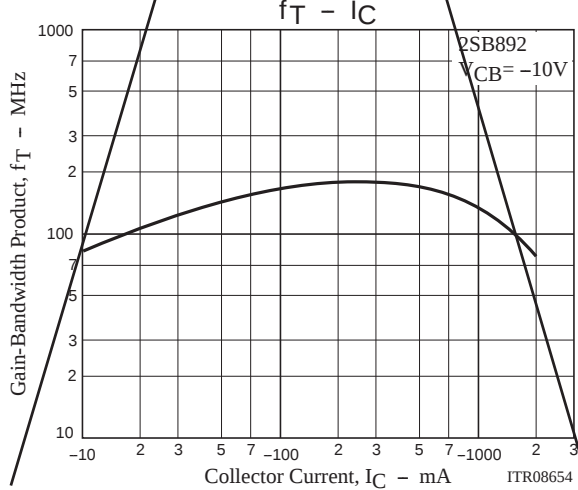
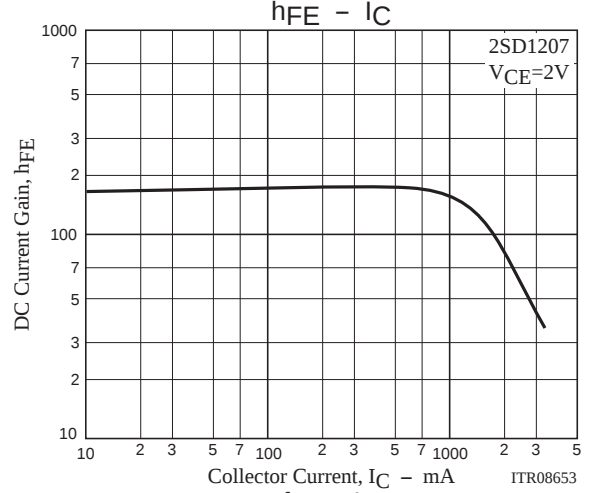
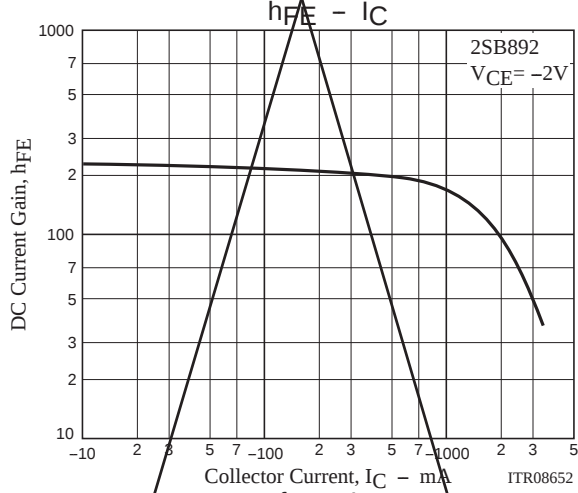
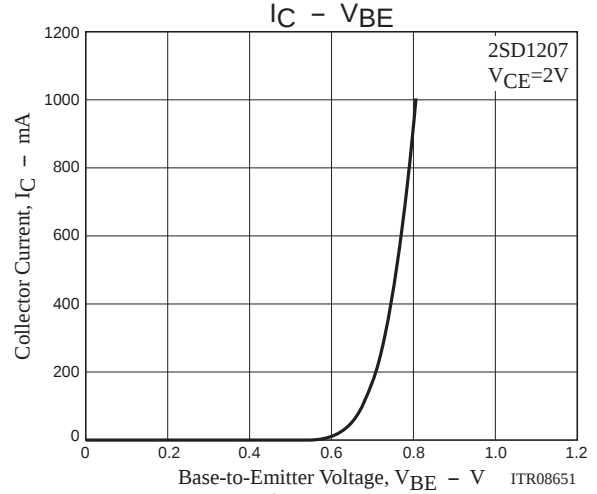
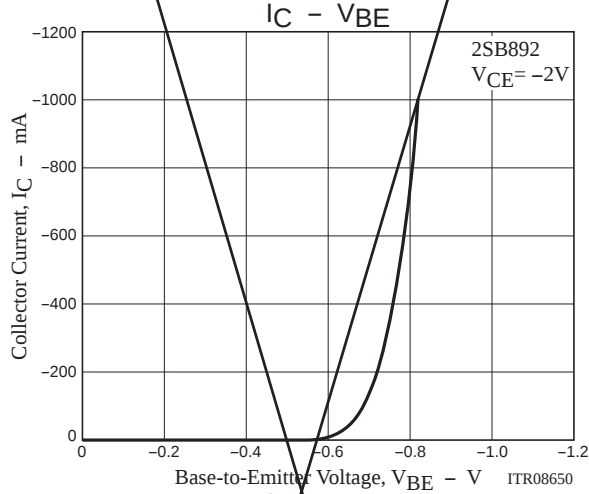
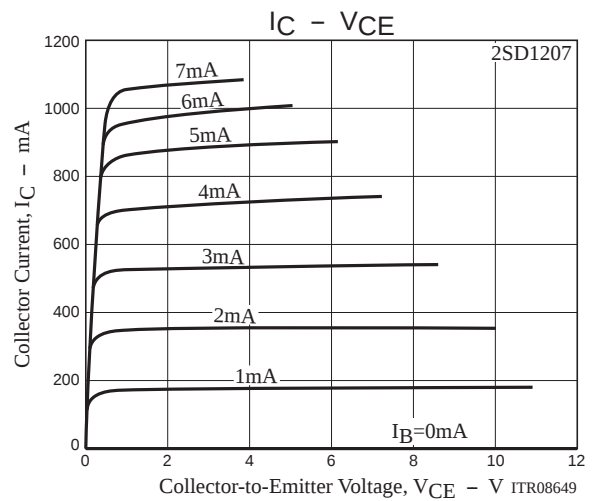
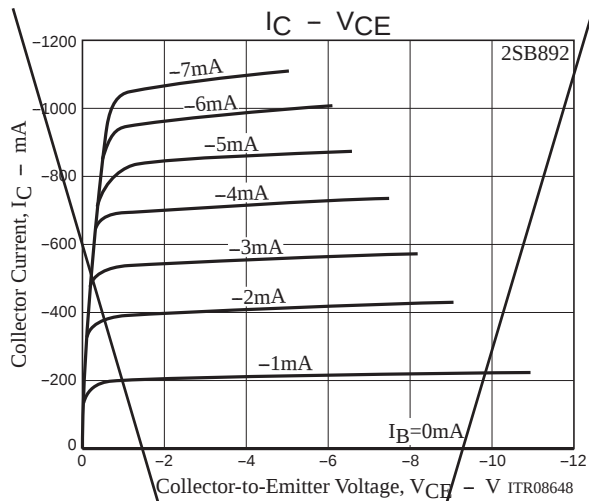
Rank	R	S	T	U
h_{FE}	100 to 200	140 to 280	200 to 400	280 to 560

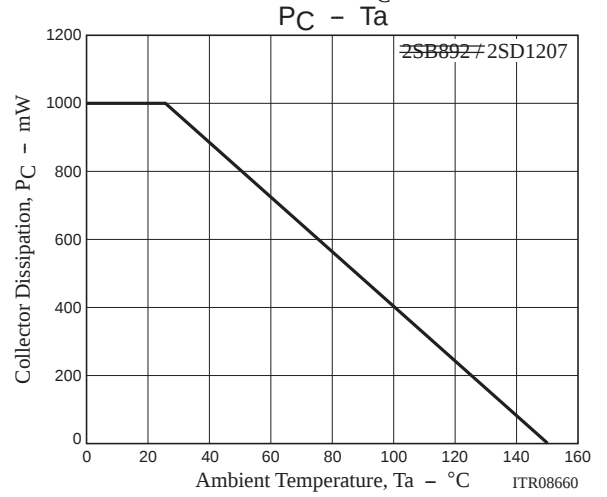
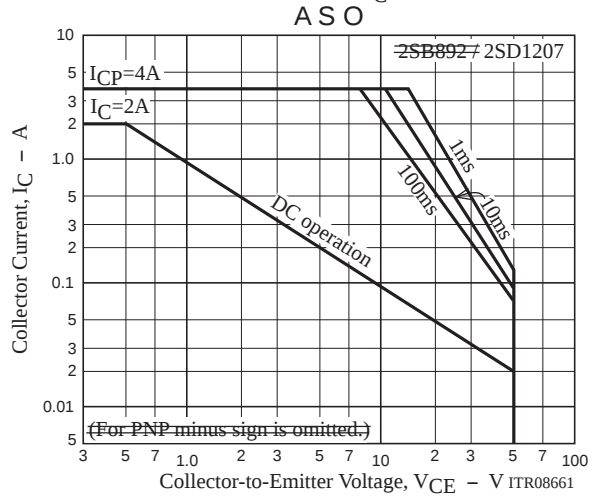
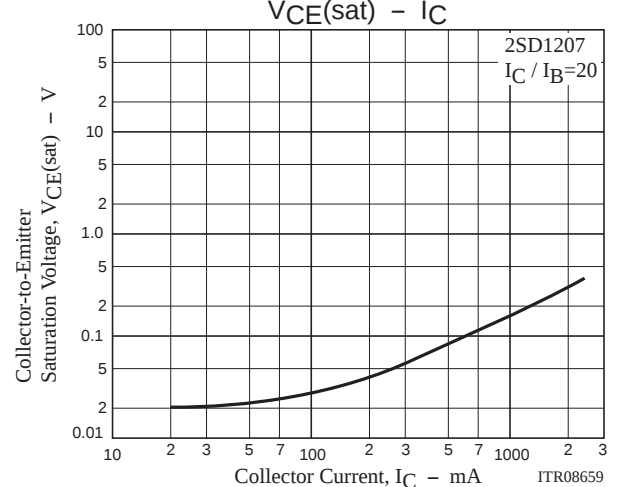
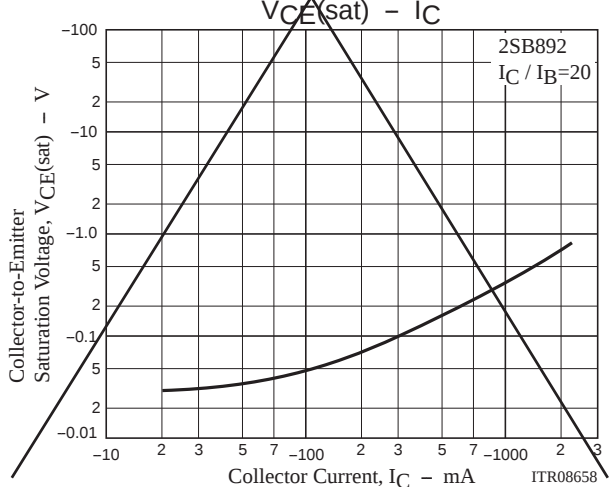
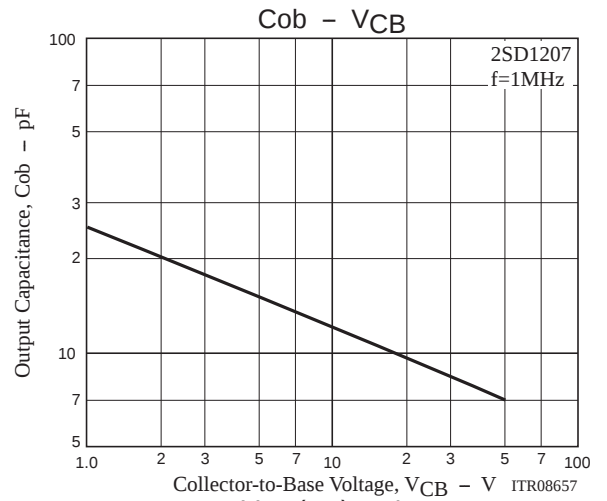
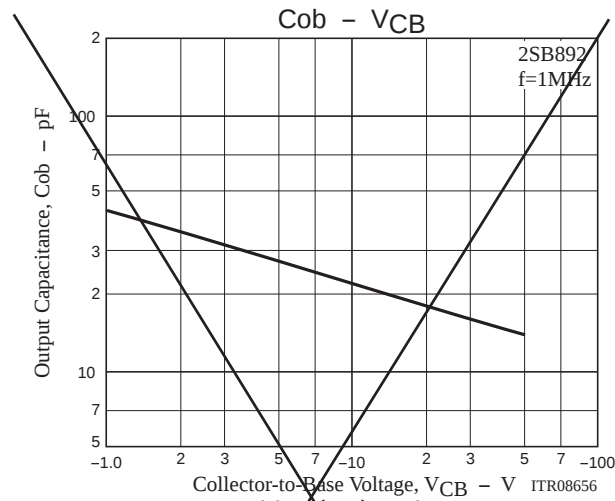
Package Dimensions

unit : mm (typ)
7520-002



2SB892+2SD1207





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